DISCRETE SEMICONDUCTORS

DATA SHEET

BF994SN-channel dual-gate MOS-FET

Product specification

July 1993



N-channel dual-gate MOS-FET

BF994S

FEATURES

• Protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

APPLICATIONS

- VHF applications such as:
 - VHF television tuners
 - Professional communication equipment.

PINNING

| PIN | SYMBOL | DESCRIPTION |
|-----|------------|-------------|
| 1 | s, b | source |
| 2 | d | drain |
| 3 | 92 | gate 2 |
| 4 | 9 1 | gate 1 |

DESCRIPTION

Depletion type field-effect transistor in a plastic SOT143 microminiature package with interconnected source and substrate.

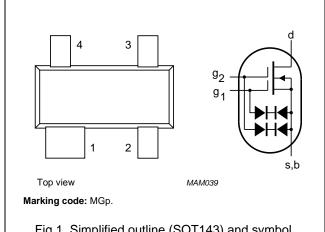


Fig.1 Simplified outline (SOT143) and symbol.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|--------------------|-----------------------------|--|------|------|------|
| V _{DS} | drain-source voltage | | _ | 20 | V |
| I_D | drain current | | | 30 | mA |
| P _{tot} | total power dissipation | up to $T_{amb} = 60 ^{\circ}C$ | _ | 200 | mW |
| Tj | junction temperature | | _ | 150 | °C |
| Y _{fs} | transfer admittance | $f = 1 \text{ kHz}; I_D = 10 \text{ mA}; V_{DS} = 15 \text{ V}; V_{G2-S} = 4 \text{ V}$ | 18 | - | mS |
| C _{ig1-s} | input capacitance at gate 1 | $f = 1 \text{ MHz}; I_D = 10 \text{ mA}; V_{DS} = 15 \text{ V}; V_{G2-S} = 4 \text{ V}$ | 2.5 | 3 | pF |
| C _{rs} | feedback capacitance | $f = 1 \text{ MHz}; I_D = 10 \text{ mA}; V_{DS} = 15 \text{ V}; V_{G2-S} = 4 \text{ V}$ | 25 | - | fF |
| F | noise figure | $f = 200 \text{ MHz}; G_S = 2 \text{ mS}; B_S = B_{Sopt};$ $I_D = 10 \text{ mA}; V_{DS} = 15 \text{ V}; V_{G2-S} = 4 \text{ V}$ | 1 | _ | dB |

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LIMITING VALUES

In according with the Absolute Maximum Rating System (IEC 134).

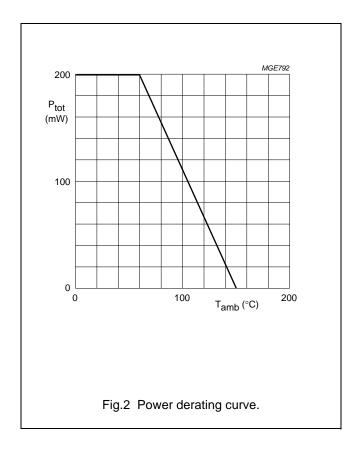
| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|---------------------------|--|------|------|------|
| V_{DS} | drain-source voltage | | _ | 20 | V |
| I _D | drain current (DC) | | _ | 30 | mA |
| I _{D(AV)} | average drain current | | _ | 30 | mA |
| I _{G1-S} | gate 1-source current | | _ | ±10 | mA |
| I _{G2-S} | gate 2-source current | | - | ±10 | mA |
| P _{tot} | total power dissipation | up to T _{amb} = 60 °C; note 1 | _ | 200 | mW |
| T _{stg} | storage temperature range | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|---------------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air; note 1 | 460 | K/W |

Note to the Limiting values and the Thermal characteristics

1. Device mounted on a ceramic substrate of $8 \times 10 \times 0.7$ mm.



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STATIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------------|---------------------------------|--|------|------|------|
| I _{G1-SS} | gate 1 cut-off currents | $V_{G1-S} = \pm 5 \text{ V}; V_{G2-S} = V_{DS} = 0$ | _ | ±50 | nA |
| I _{G2-SS} | gate 2 cut-off currents | $V_{G2-S} = \pm 5 \text{ V}; V_{G1-S} = V_{DS} = 0$ | _ | ±50 | nA |
| V _{(BR)G1-SS} | gate 1-source breakdown voltage | $I_{G1-SS} = \pm 10 \text{ mA}; V_{G2-S} = V_{DS} = 0$ | ±6 | ±20 | V |
| V _{(BR)G2-SS} | gate 2-source breakdown voltage | $I_{G2-SS} = \pm 10 \text{ mA}; V_{G1-S} = V_{DS} = 0$ | ±6 | ±20 | V |
| I _{DSS} | drain-source cut-off voltage | V _{DS} = 15 V; V _{G1-S} = 0; V _{G2-S} = 4 V | 4 | 20 | mA |
| V _{(P)G1-S} | gate 1-source cut-off voltage | $I_D = 20 \mu A; V_{DS} = 15 V; V_{G2-S} = 4 V$ | _ | -2.5 | V |
| V _{(P)G2-S} | gate 2-source cut-off voltage | $I_D = 20 \mu A; V_{DS} = 15 V; V_{G1-S} = 0$ | _ | -2 | V |

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; V_{G2-S} = 4 V; T_{amb} = 25 °C.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|-----------------------------|---|------|------|------|------|
| Y _{fs} | transfer admittance | f = 1 kHz | 15 | 18 | _ | mS |
| C _{ig1-s} | input capacitance at gate 1 | f = 1 MHz | _ | 2.5 | 3 | pF |
| C _{ig2-s} | input capacitance at gate 2 | f = 1 MHz | _ | 1.2 | _ | pF |
| C _{rs} | feedback capacitance | f = 1 MHz | _ | 25 | _ | fF |
| Cos | output capacitance | f = 1 MHz | _ | 1 | _ | pF |
| F | noise figure | $f = 200 \text{ MHz}; G_S = 2 \text{ mS}; B_S = B_{Sopt}$ | _ | 1 | _ | dB |
| G _p | power gain | $f = 200 \text{ MHz}; G_S = 2 \text{ mS}; B_S = B_{Sopt}; G_L = 0.5 \text{ mS}; B_L = B_{Lopt}$ | _ | 25 | _ | dB |

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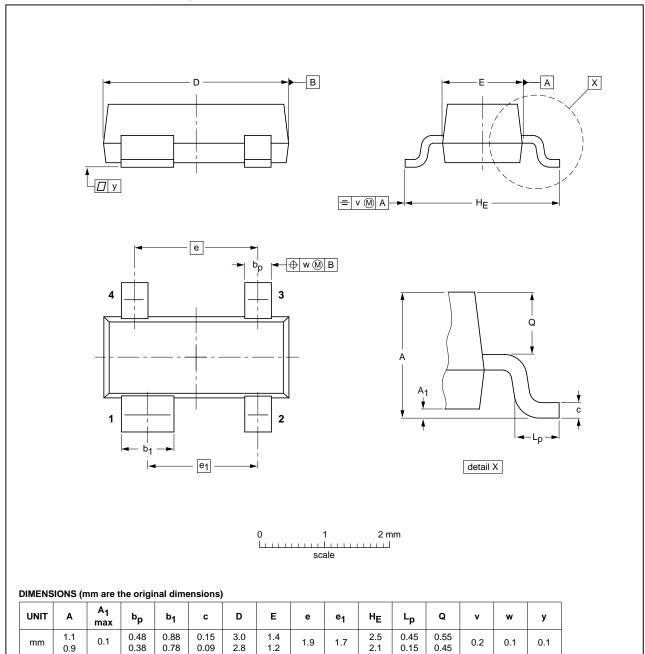
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PACKAGE OUTLINE

Plastic surface-mounted package; 4 leads

SOT143B

0.1



| OUTLINE | REFERENCES | | | EUROPEAN | ISSUE DATE | |
|---------|------------|-------|-------|----------|------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT143B | | | | | | 04-11-16 06-03-16 |

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0.1

0.38

0.78

mm

0.9

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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